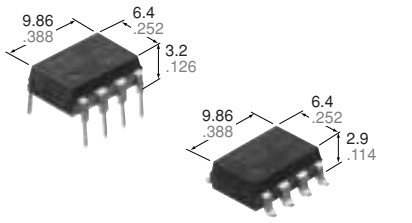
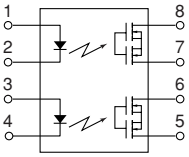
Panasonic
ideas for life

General use and economy type. DIP (2 Form B) 8-pin type. Reinforced insulation 5,000V type.

GU-E PhotoMOS (AQW414EH)



mm inch



FEATURES

1. Reinforced insulation 5,000 V type
More than 0.4 mm internal insulation distance between inputs and outputs. Con-forms to EN41003, EN60950 (reinforced insulation).

2. Compact 8-pin DIP size
The device comes in a compact (W)6.4×(L)9.86×(H)3.2 mm (W).252×(L).388×(H).126 inch, 8-pin DIP size (through hole terminal type).

3. Applicable for 2 Form B use as well as two independent 1 Form B use

4. Controls low-level analog signals
PhotoMOS relays feature extremely low closed-circuit offset voltage to enable control of low-level analog signals without distortion.

5. High sensitivity, high speed response.
Can control a maximum 0.13 A load current with a 5 mA input current. Fast operation speed of 0.8 ms (typical).

6. Low-level off state leakage current

TYPICAL APPLICATIONS

- Modem
- Telephone equipment
- Security equipment
- Sensors

TYPES

Type	I/O isolation voltage	Output rating*		Part No.				Packing quantity	
				Through hole terminal	Surface-mount terminal				
		Load voltage	Load current	Tube packing style		Tape and reel packing style		Tube	Tape and reel
						Picked from the 1/2/3/4-pin side	Picked from the 5/6/7/8-pin side		
AC/DC type	Reinforced 5,000 V	400 V	100 mA	AQW414EH	AQW414EHA	AQW414EHAX	AQW414EHAZ	1 tube contains 40 pcs. 1 batch contains 400 pcs.	1,000 pcs.

*Indicate the peak AC and DC values.
Note:
For space reasons, the SMD terminal shape indicator "A" and the package type indicator "X" and "Z" are omitted from the seal.

RATING

1. Absolute maximum ratings (Ambient temperature: 25°C 77°F)

Item		Symbol	AQW414EH (A)	Remarks
Input	LED forward current	I_F	50mA	
	LED reverse voltage	V_R	5V	
	Peak forward current	I_{FP}	1A	f =100 Hz, Duty factor = 0.1%
	Power dissipation	P_{in}	75mW	
Output	Load voltage (peak AC)	V_L	400 V	
	Continuous load current	I_L	0.1 A (0.13 A)	Peak AC, DC ( ): in case of using only 1 channel.
	Peak load current	I_{peak}	0.3 A	100 ms (1 shot), V_L= DC
	Power dissipation	P_{out}	800mW	
Total power dissipation		P_T	850mW	
I/O isolation voltage		V_{iso}	5,000 V AC	
Temperature limits	Operating	T_{opr}	–40°C to +85°C –40°F to +185°F	Non-condensing at low temperatures
	Storage	T_{stg}	–40°C to +100°C –40°F to +212°F	

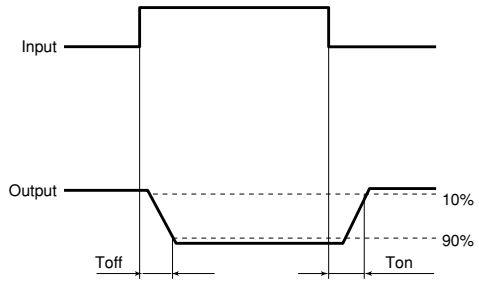
2. Electrical characteristics (Ambient temperature: 25°C 77°F)

Item			Symbol	AQW414EH (A)	Condition
Input	LED operate (OFF) current	Typical	I_{Foff}	1.3mA	I_L=Max.
		Maximum		3.0mA	
	LED reverse (ON) current	Minimum	I_{Fon}	0.4mA	I_L=Max.
		Typical		1.2mA	
	LED dropout voltage	Typical	V_F	1.25 (1.14 V at I_F=5mA)	I_F=50mA
		Maximum		1.5V	
Output	On resistance	Typical	R_{on}	26Ω	I_F=0mA I_L=Max. Within 1 s on time
		Maximum		35Ω	
	Off state leakage current	Maximum	I_{Leak}	10μA	I_F=5mA V_L=Max.
Transfer characteristics	Turn on time*	Typical	T_{off}	0.8ms	I_F=0mA→5mA I_L=Max.
		Maximum		3.0ms	
	Turn off time*	Typical	T_{on}	0.2ms	I_F=5mA→0mA I_L=Max.
		Maximum		1.0ms	
	I/O capacitance	Typical	C_{iso}	0.8pF	f =1MHz V_B =0V
		Maximum		1.5pF	
	Initial I/O isolation resistance	Minimum	R_{iso}	1,000MΩ	500V DC

Note: Recommendable LED forward current I_F= 5 to 10mA.

For type of connection

*Operate/Reverse time

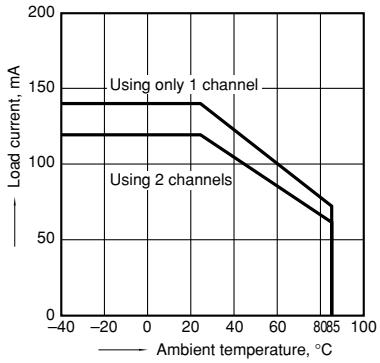


■ For Dimensions
■ For Schematic and Wiring Diagrams
■ For Cautions for Use

REFERENCE DATA

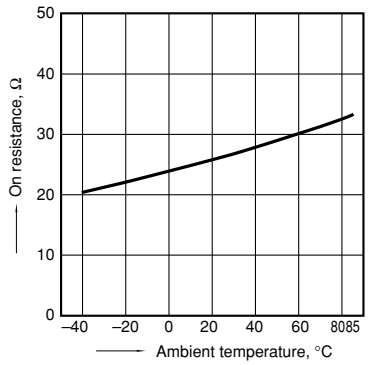
1. Load current vs. ambient temperature characteristics

Allowable ambient temperature: –40°C to +85°C
–40°F to +185°F



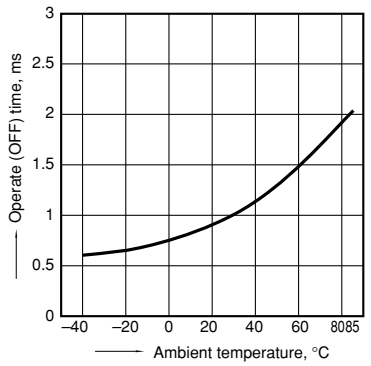
2. On resistance vs. ambient temperature characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
LED current: 0 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



3. Operate (OFF) time vs. ambient temperature characteristics

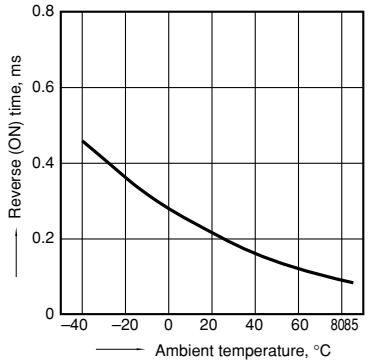
LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



GU-E PhotoMOS (AQW414EH)

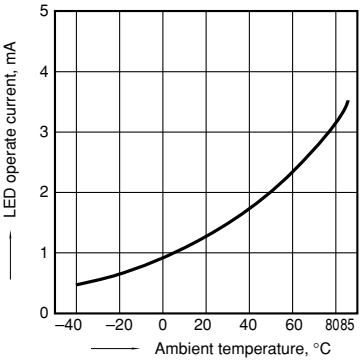
4. Reverse (ON) time vs. ambient temperature characteristics

LED current: 5 mA; Load voltage: Max. (DC);
Continuous load current: Max. (DC)



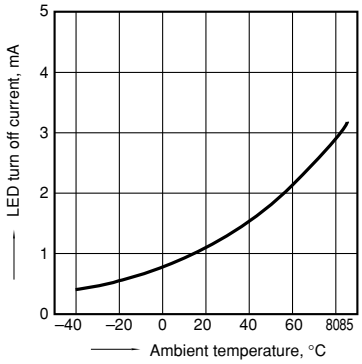
5. LED operate current vs. ambient temperature characteristics

Load voltage: Max. (DC);
Continuous load current: Max. (DC)



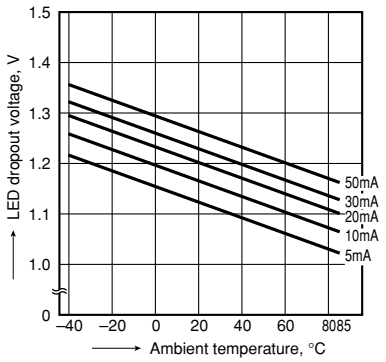
6. LED turn off current vs. ambient temperature characteristics

Load voltage: Max. (DC);
Continuous load current: Max. (DC)



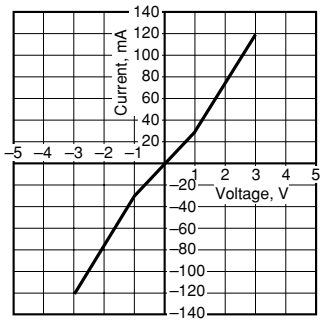
7. LED dropout voltage vs. ambient temperature characteristics;

LED current: 5 to 50 mA



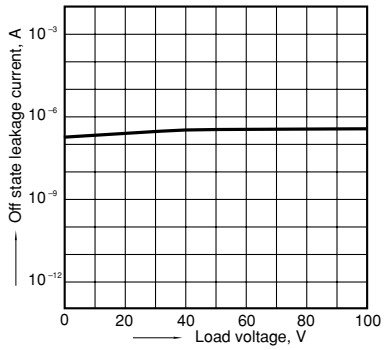
8. Current vs. voltage characteristics of output at MOS portion

Measured portion: between terminals 5 and 6, 7 and 8;
Ambient temperature: 25°C 77°F



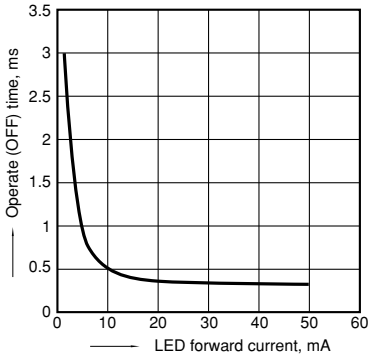
9. Off state leakage current vs. load voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Ambient temperature: 25°C 77°F



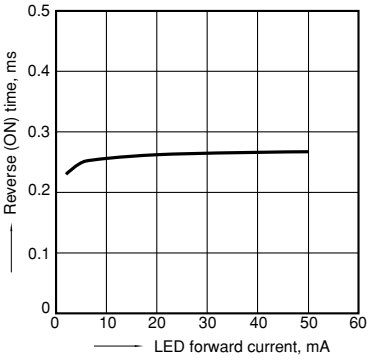
10. Operate (OFF) time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Load voltage: Max. (DC); Continuous load current:
Max. (DC); Ambient temperature: 25°C 77°F



11. Reverse (ON) time vs. LED forward current characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Load voltage: Max. (DC); Continuous load current:
Max. (DC); Ambient temperature: 25°C 77°F



12. Output capacitance vs. applied voltage characteristics

Measured portion: between terminals 5 and 6, 7 and 8;
Frequency: 1 MHz; Ambient temperature: 25°C 77°F